Approved for use through 10/31/2002. OMB 0651-0031 s sign (+) inside this box -> [+] U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE perwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number. Application Number 09/690,580 TRANSMITTAL TIAIL HODDEtober 17, 2000 Filing Date **FORM** First Named Inventor Vladislav Vashchenko et al. (to be used for all correspondence after initial filing) Group Art Unit 2814 **Examiner Name** D. Farahani Total Number of Pages in This Submission Attorney Docket Number 072219-0276286 (P04802) ENCLOSURES (check all that apply) Assignment Papers Fee Transmittal Form (for an Application) Group Appeal Communication to Board of Fee Attached Drawing(s) 4 sheets (Informal) Appeals and Interferences Amendment/Response to Paper No. Appeal Communication to Group Licensing-related Papers (Appeal Notice, Brief, Reply Brief) Petition Routing Slip (PTO/SB/69) After Final (Response) Proprietary Information and Accompanying Petition Petition to Convert to a Affidavits/declaration(s) ☐ Status Letter Provisional Application Power of Attorney, Revocation Other Enclosure(s) Extension of Time Request Change of Correspondence Address (please identify below): Terminal Disclaimer **Return Receipt Postcard** Express Abandonment Request Certificate of Mailing Request for Refund ☐ Information Disclosure Statement CD, Number of CD(s) Certified Copy of Priority Please charge any deficiencies in fees or overpayment to Deposit Account No. 03-3975 (a copy of this transmittal is Document(s) Remarks enclosed for this purpose). Response to Missing Parts/ Incomplete Application Response to Missing Parts under 37 CFR 1.52 or 1.53 SIGNATURE OF APPLICANT, ATTORNEY, OR AGENT

Firm Mark C. Pickering, Reg. No. 36,239 Individual name Signature Date January 16, 2002 CERTIFICATE OF MAILING

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE 7 2

In repatent Application of:

Vladislav Vashchenko, et al.

Appln. No.: 09/690,580

Filed: October 17, 2000

For: BIPOLAR TRANSISTOR-BASED ELECTROSTATIC DISCHARGE (ESD) PROTECTION STRUCTURE WITH A

HEAT SINK

Group Art Unit: 2814

Examiner: D. Farahani

RESPONSE TO OFFICE ACTION MAILED

OCTOBER 24, 2001

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service, postage prepaid, in an envelope, addressed to box Non-For-Arma commissioner for Patents,

Washington D.C. 20231-9999 on 01-16-02

Dated: 01-16-02

Commissioner for Patents Washington, D.C. 20231

Dear Sir:

In response to the Official Action mailed October 24, 2001, please amend the above-identified application as follows:

In the Claims

Claims 7-8 have been cancelled.

Please add the following new claims:

- --9. An electrostatic discharge device formed in a first semiconductor material, the device comprising:
- a collector region of a first conductivity type formed in the first semiconductor material;
 - a base region of a second conductivity type formed in the collector region;
- an emitter formed on the first semiconductor material on the base region, the emitter having a top surface;
- a base extender formed on the first semiconductor material on the base region, the base extender being formed from a second semiconductor material that is different from the first semiconductor material;

Atty. Docket No.: 072219-0276286

(P04802) 10581953V1 -1-